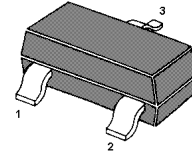


MMBTSA812

PNP Silicon Epitaxial Planar Transistor

for audio frequency, general purpose amplifier.

The transistor is subdivided into four groups O, Y, G and L, according to its DC current gain.



1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	50	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{Stg}	-55 to +150	$^\circ\text{C}$

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MMBTSA812

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

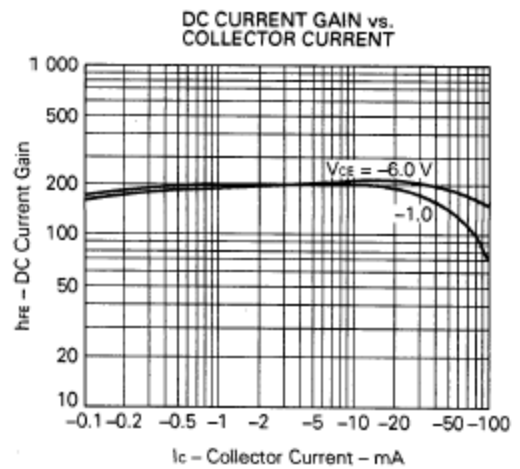
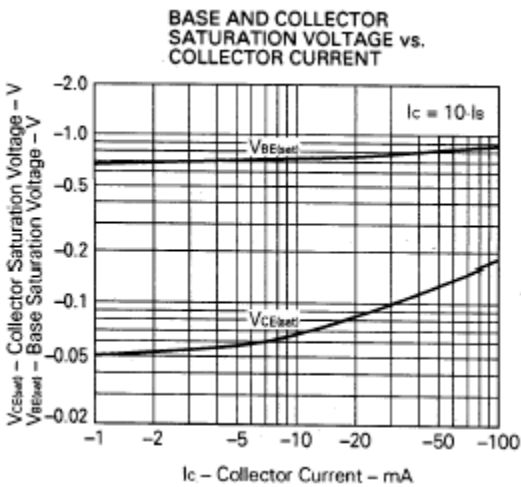
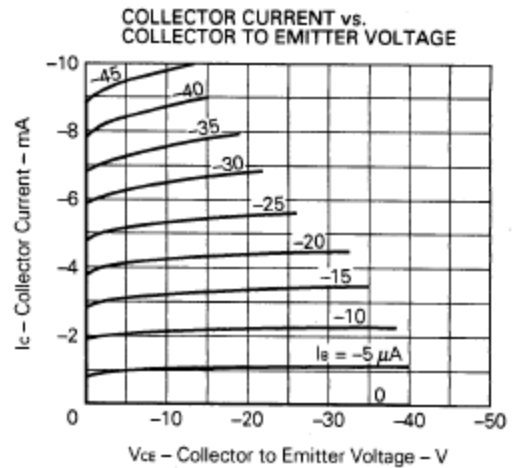
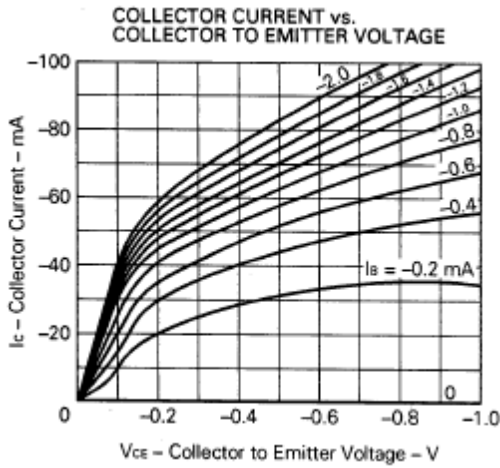
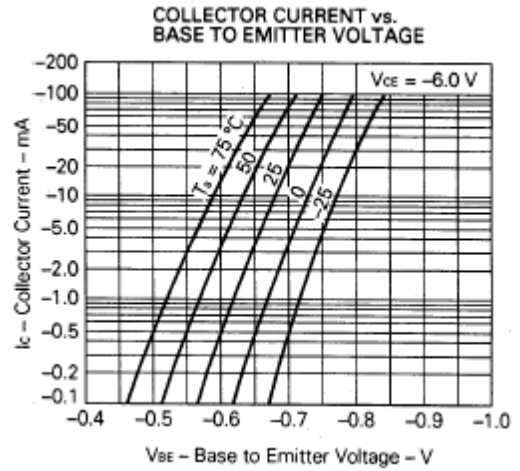
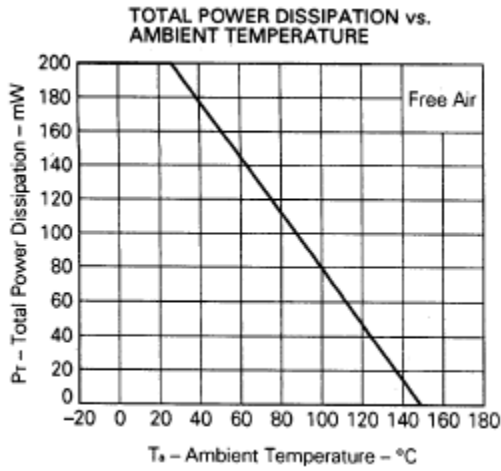
	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE}=6\text{V}$, $-I_C=1\text{mA}$					
Current Gain Group O	h_{FE}	90	-	180	-
Y	h_{FE}	135	-	270	-
G	h_{FE}	200	-	400	-
L	h_{FE}	300	-	600	-
Collector Cutoff Current at $-V_{CB}=60\text{V}$	$-I_{CBO}$	-	-	0.1	μA
Emitter Cutoff Current at $-V_{EB}=5\text{V}$	$-I_{EBO}$	-	-	0.1	μA
Collector Saturation Voltage at $-I_C=100\text{mA}$, $-I_B=10\text{mA}$	$-V_{CE(sat)}$	-	-	0.3	V
Base Emitter Voltage at $-V_{CE}=6\text{V}$, $-I_C=1\text{mA}$	$-V_{BE}$	0.58	-	0.68	V
Gain Bandwidth Product at $-V_{CE}=6\text{V}$, $-I_C=10\text{mA}$	f_T	-	180	-	MHz
Output Capacitance at $-V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_{OB}	-	4.5	-	pF

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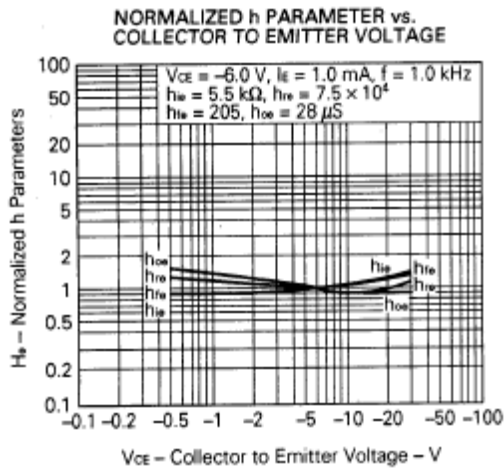
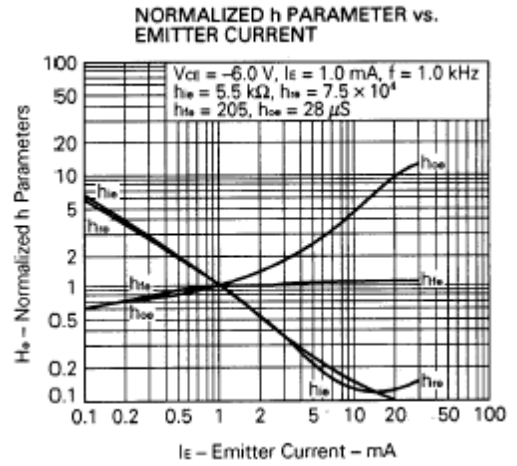
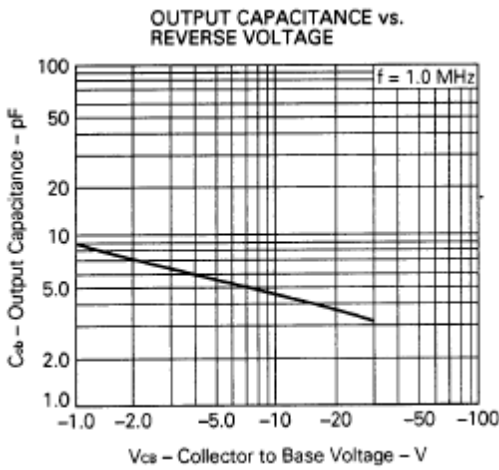
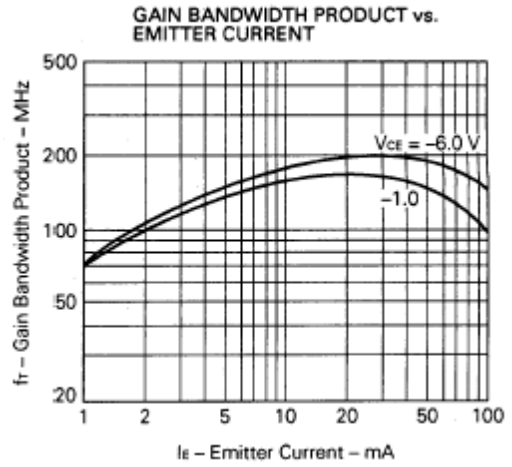
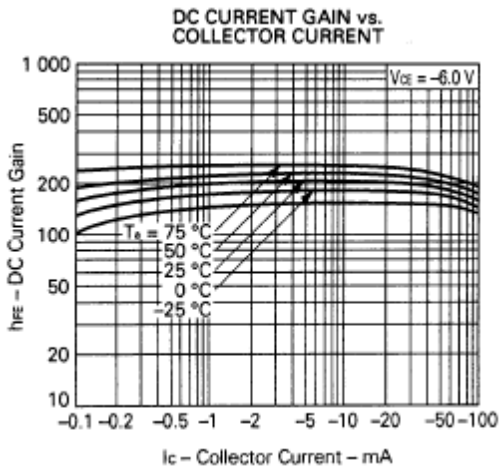
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